Ordering number : ENN8373

SANYO Semiconductors
DATA SHEET

SS0310M — Schottky Barrier Diode 100V, 0.3A Rectifier

Applications

- High frequency rectification (switching regulators, converters, choppers).

Features

- Low Switching noise.
- Low forward voltage (I_F=0.3A, V_F max=0.57V).
- Ultrasmall package permitting SS0310M applied sets to be made small and slim.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		100	V
Nonrepetitive Peak Reverse Surge Voltage	V_{RSM}		100	V
Average Output Current	I_O		0.3	A
Surge Forward Current	I_{FSM}	50Hz sine wave, 1 cycle	10	A
Junction Temperature	Tj		-55 to +125	°C
Storage Temperature	Tstg		-55 to +125	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Reverse Voltage	V_R	I_R=0.5mA	100			V
Forward Voltage	V_F	I_F=0.3A		0.52	0.57	V
Reverse Current	I_R	V_R=50V			600	μA
Interterminal Capacitance	C	V_R=10V, f=1MHz		20		pF
Reverse Recovery Time	t_{rr}	I_F=I_R=100mA, See specified Test Circuit.			10	ns
Thermal Resistance	Rth(j-a)1	Mounted in Cu-foiled area of 0.72mm²X0.03mm on glass epoxy board		94.7		°C / W
	Rth(j-a)2	Mounted on a ceramic board (1000mm²X0.8mm)		67.7		°C / W

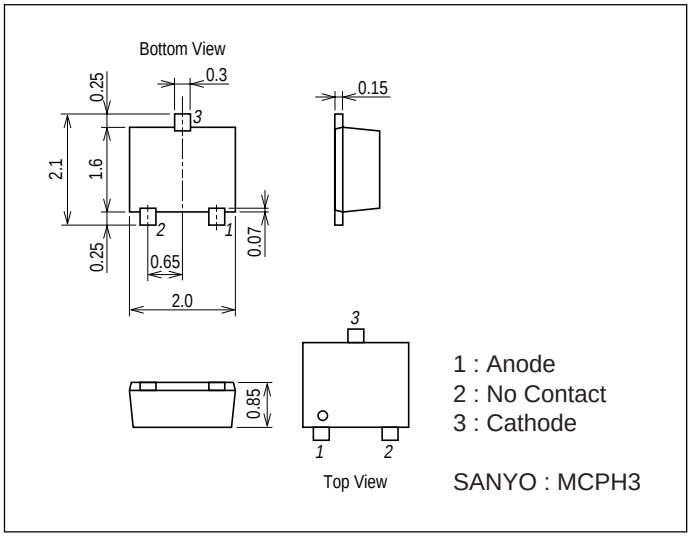
Marking : SH

SANYO Electric Co.,Ltd. Semiconductor Company
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

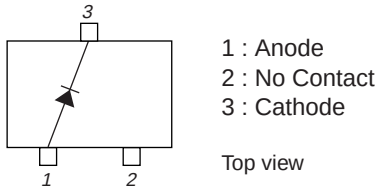
Package Dimensions

unit : mm

7019-001



Electrical Connection



t_{rr} Test Circuit